

# Supplementary Information

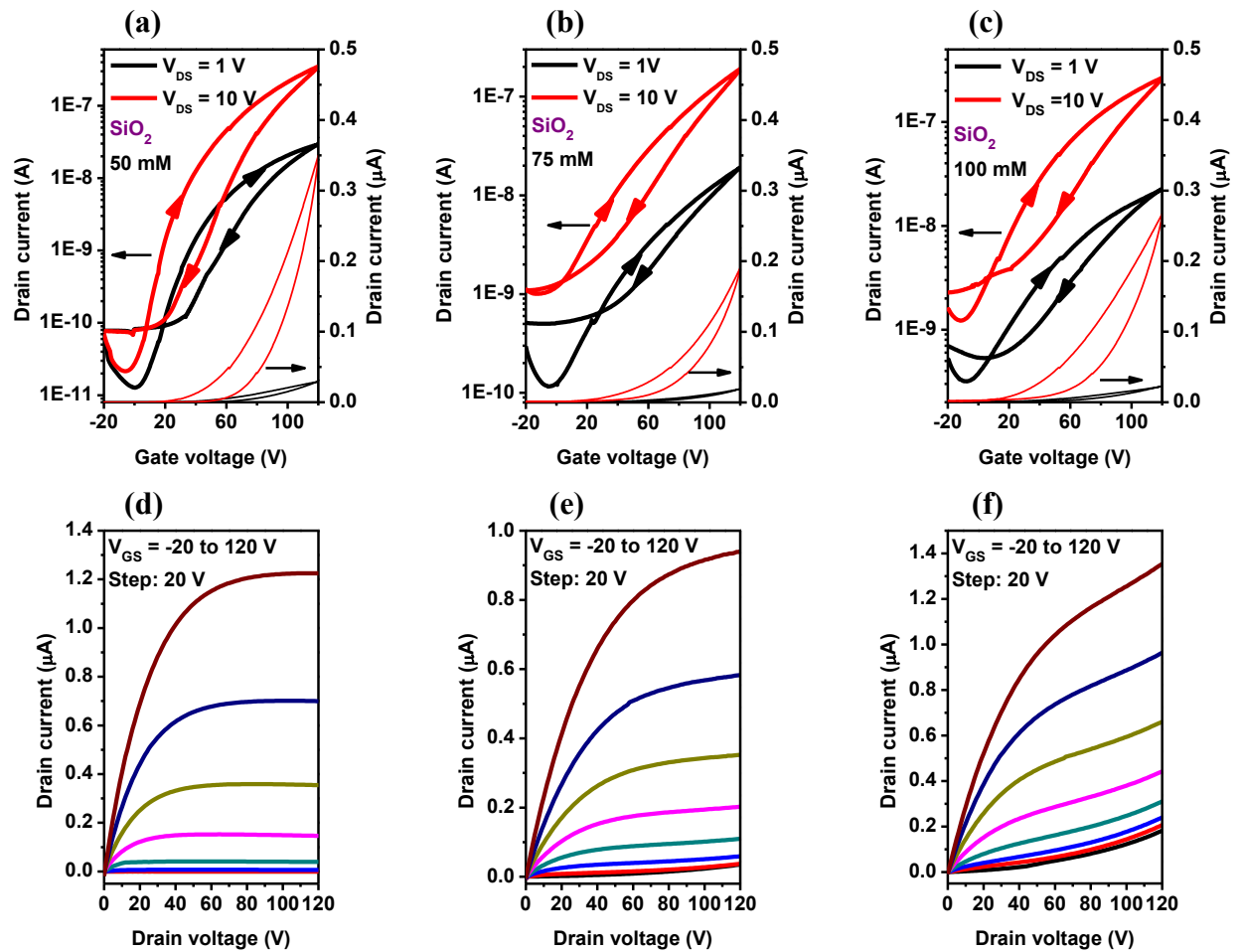
## Improved Electrical Properties of EHD Jet-Patterned MoS<sub>2</sub> Thin-Film Transistors with Printed Ag Electrodes on a High-k Dielectric

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**Figure S1.** (a-c) Transfer characteristic curves with hysteresis behavior and (d-f) output characteristic curves of SiO<sub>2</sub>-based MoS<sub>2</sub> TFTs prepared from 50 mM, 75 mM and 100 mM solution concentrations.

**Table S1** Characteristics of the SiO<sub>2</sub>-based printed MoS<sub>2</sub> TFTs.

| G/I              | Concentration<br>[mM] | $I_{on}/I_{off}$            | S-S<br>[V dec <sup>-1</sup> ] | $\mu$<br>[cm <sup>2</sup> V <sup>-1</sup> s <sup>-1</sup> ] | Hysteresis<br>[V] |
|------------------|-----------------------|-----------------------------|-------------------------------|-------------------------------------------------------------|-------------------|
| SiO <sub>2</sub> | 50                    | $(1.2 \pm 0.8) \times 10^4$ | 15.5 ± 4.4                    | 0.024 ± 0.02                                                | 29.3 ± 4.9        |
|                  | 75                    | $(9.0 \pm 5.1) \times 10^1$ | 53.2 ± 10.3                   | 0.0036 ± 0.0013                                             | 17.6 ± 3.6        |
|                  | 100                   | $(9.6 \pm 5.5) \times 10^1$ | 53 ± 12                       | 0.0072 ± 0.0017                                             | 20.3 ± 4.9        |